NSN 5962-01-394-0350

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Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
55.0/+125.0 degrees celsius
Storage Tempurature Range:
65.0/+150.0 degrees celsius
End Application:
Pacer dawn
Features Provided:
Electrostatic sensitive and bipolar and burn in, mil-std-883, class b and monolithic and programmed and tested to mil-std-883
nclosure Material:
Ceramic
nclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
nput Circuit Pattern:
20 input
Criticality Code Justification:
Feat Control of the C
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc and 210.00 milliamperes reverse current, dc absolute and 1.00 milliamperes reverse current, d
microamperes
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital, pal, memory and i/o address decode
Voltage Rating And Type Per Characteristic:
1.5 volts input and 12.0 volts input and -0.5 volts power source and 12.0 volts power source
Time Rating Per Chacteristic:
30.00 nanoseconds delay
Memory Device Type:
Pal
Special Features:
Esd; altered item from m38510/50501blx using program instructions pg6390000-01
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Shelf Life:
N/a

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Unit Of Measure:

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Demilitarization:

No

Fiig:

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